

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	"20040155244"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 15:12
S2	2	("6207586").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/17 15:16
S3	11	@ad<="20040114" and 'TFT' and 'monocrystalline silicon' and 'thermal oxide' same 'cvd' with 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 08:14
S4	9	@ad<="20040114" and 'TFT' and 'monocrystalline silicon' and 'gate insulating' with 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 15:37
S5	198	@ad<="20040114" and 'monocrystalline silicon' and 'thermal oxide' same 'cvd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 15:31
S6	4	@ad<="20040114" and 'TFT' and 'monocrystalline silicon' and 'gate' with 'thermal oxide' with 'cvd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 15:38
S7	22	@ad<="20040114" and 'TFT' and 'monocrystalline silicon' and 'gate insulating' and 'thermal oxide' and 'cvd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 15:52
S10	116	@ad<="20040114" and 'gate insulating' same 'thermal oxide' with 'cvd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 15:52
S11	4	@ad<="20040114" and 'tft;' and 'monocrystalline silicon' with 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 15:54
S12	70	@ad<="20040114" and 'monocrystalline silicon' with 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 15:54

S13	34	@ad<="20040114" and 'TFT' and 'monocrystalline silicon' and 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/17 16:05
S14	112	@ad<="20040114" and 'TFT' and 'monocrystalline silicon' and 'oxidized'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 07:58
S15	1	"20030116719".PN.	US-PGPUB	OR	ON	2005/05/17 16:05
S16	1	"20030085397".PN.	US-PGPUB	OR	ON	2005/05/17 16:05
S17	138	@ad<="20040114" and 'LCD' and 'monocrystalline silicon' and 'oxide' same 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 08:40
S18	15	@ad<="20040114" and 'electro-optical' and 'monocrystalline silicon' and 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 08:40
S19	9	@ad<="20040114" and 'LCD' and 'monocrystalline silicon' and 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 08:40
S20	131	@ad<="20040114" and 'LCD' and 'monocrystalline silicon' and 'oxide' with 'nitride'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 08:40
S22	1	'wo 200011709'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 09:05
S23	1	"5432625".PN.	USPAT; USOCR	OR	ON	2005/05/18 10:28
S24	3	@ad<="20040114" and 'TFT' and 'monocrystal' with 'silicon' and 'insulating' with 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 14:25
S25	102	@ad<="20040114" and 'TFT' and 'single' with 'crystal' with 'silicon' and 'insulating' with 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 11:23
S26	80	@ad<="20040114" and 'TFT' and 'single' with 'crystal' with 'silicon' and 'insulating' with 'thermal oxide' and 'oxide' with 'cvd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 15:58

S27	3	("6011275").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/18 11:52
S28	9251	@ad<="20040114" and (257/59). ccls. or (257/347).ccls. or (257/64). ccls. or (257/65).ccls. or (257/66). ccls. or (257/67).ccls. or (257/72). ccls. or (257/E21.413).ccls. or (257/E21.703).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 11:55
S29	704	@ad<="20040114" and (257/57). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:04
S30	1155	@ad<="20040114" and (257/79). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/18 12:04
S31	81	@ad<="20040114" and 'TFT' and 'single' with 'crystal' with 'silicon' and 'insulating' with 'thermal oxide' and 'oxide' with 'cvd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 14:26
S32	3	@ad<="20040114" and 'TFT' and 'monocrystal' with 'silicon' and 'insulating' with 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 16:02
S33	36	@ad<="20040114" and 'TFT' and 'single' with 'crystal' with 'silicon' and 'insulating' with 'thermal oxide' and 'oxide' with 'cvd' and 'LDD'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 08:20
S34	9	("6077731").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/02 14:58
S45	110	@ad<="20040114" and 'single crystal' with 'silicon' same 'mono'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 15:55
S46	81	@ad<="20040114" and 'TFT' and 'single' with 'crystal' with 'silicon' and 'insulating' with 'thermal oxide' and 'oxide' with 'cvd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 15:58

S47	855	@ad<="20040114" and 'TFT' and 'monocrystalline'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 16:02
S48	61	@ad<="20040114" and 'TFT' and 'monocrystalline' and 'gate' with 'thermal' with 'cvd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 16:05
S49	7	@ad<="20040114" and 'TFT' and 'monocrystalline' and 'gate' with 'thermal' with 'cvd' and 'idd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 16:05
S50	38	@ad<="20040114" and 'TFT' and 'monocrystalline' and 'thermal' with 'cvd' and 'idd'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 16:05
S51	0	@ad<="20040114" and 'TFT' and 'insulating gate' with 'capacitor line'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 07:59
S52	183	@ad<="20040114" and 'TFT' and 'gate insulating' same 'capacitor line'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 08:00
S53	136	@ad<="20040114" and 'TFT' and 'gate insulating' with 'capacitor line'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 08:00
S54	31	@ad<="20040114" and 'TFT' with 'gate insulating' with 'capacitor line'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/03 08:00
S55	183	@ad<="20040114" and 'TFT' and ('monocrystalline' or 'monocrystal' or 'crystallinity') with 'silicon' and 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 15:57
S56	71	@ad<="20040114" and 'TFT' and ('monocrystalline' or 'monocrystal' or 'crystallinity') with 'silicon' and 'thermal oxide' same 'cvd' same 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 15:59
S57	1	@ad<="20040114" and 'TFT' same 'monocrystalline' with 'silicon' and 'thermal oxide' same 'cvd' same 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 16:00

S58	8	@ad<="20040114" and 'TFT' same 'monocrystalline' with 'silicon' and 'thermal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 16:02
S59	200	@ad<="20040114" and 'TFT' same 'monocrystalline' with 'silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 16:02
S60	128	@ad<="20040114" and 'TFT' with 'monocrystalline' with 'silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 16:02
S61	111	@ad<="20040114" and 'TFT' with 'monocrystalline silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 16:07
S62	37	@ad<="20040114" and 'TFT' and 'monocrystalline silicon' same 'channel' and 'LDD'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 16:22
S63	8	@ad<="20040114" and 'TFT' and 'monocrystalline silicon' same 'active layer'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 08:13
S64	0	@ad<="20040114" and 'TFT' same 'monocrystalline semiconductor' with 'active layer' same 'thermal oxide' same 'cvd' with 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 08:13
S65	0	@ad<="20040114" and 'TFT' same 'monocrystalline' with 'active layer' same 'thermal oxide' same 'cvd' with 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 08:14
S66	0	@ad<="20040114" and 'TFT' same 'monocrystalline' with 'active' same 'thermal oxide' same 'cvd' with 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 08:14
S67	0	@ad<="20040114" and 'TFT' and 'monocrystalline' with 'active' same 'thermal oxide' same 'cvd' with 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 08:14
S68	11	@ad<="20040114" and 'TFT' and 'monocrystalline silicon' and 'thermal oxide' same 'cvd' with 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 08:14

S69	0	@ad<="20040114" and 'TFT' and 'monocrystalline' with 'active' and 'thermal oxide' same 'cvd' with 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 08:14
S70	8	@ad<="20040114" and 'TFT' and 'mono' with 'crystal' with 'silicon' and ('insulating' or 'dielectric') with 'thermal oxide' and ('oxide' or 'nitride') with 'cvd' and 'LDD'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/06 08:21